

# VLSI LAB Experiment-6 AND, OR, & XOR Gates using Pass Transistors and Transmission Gates

Group Number: 2

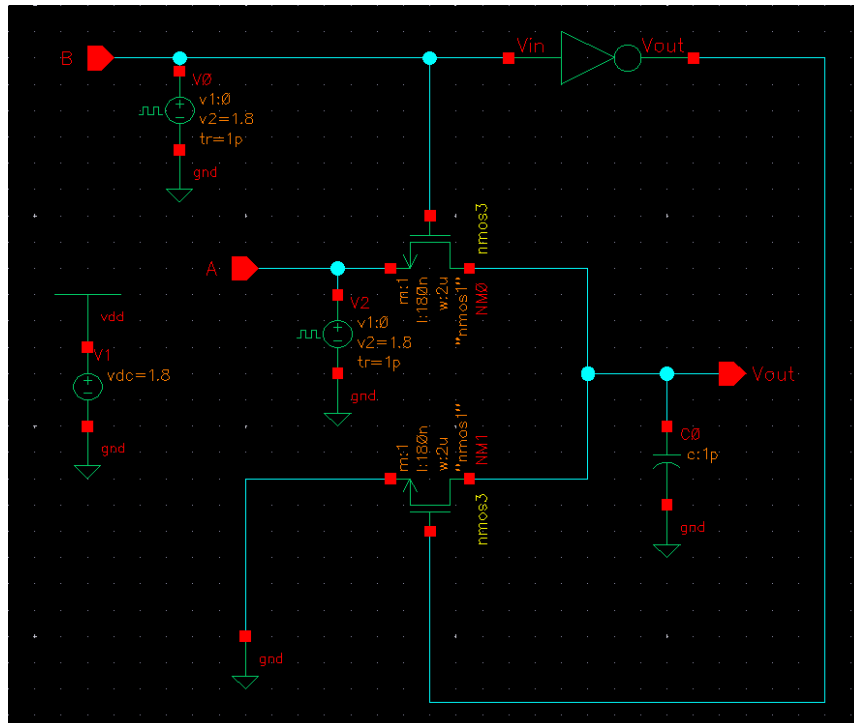
Group Members:

Thathapudi Sanjeev Paul Joel - 2020AAPS0120H

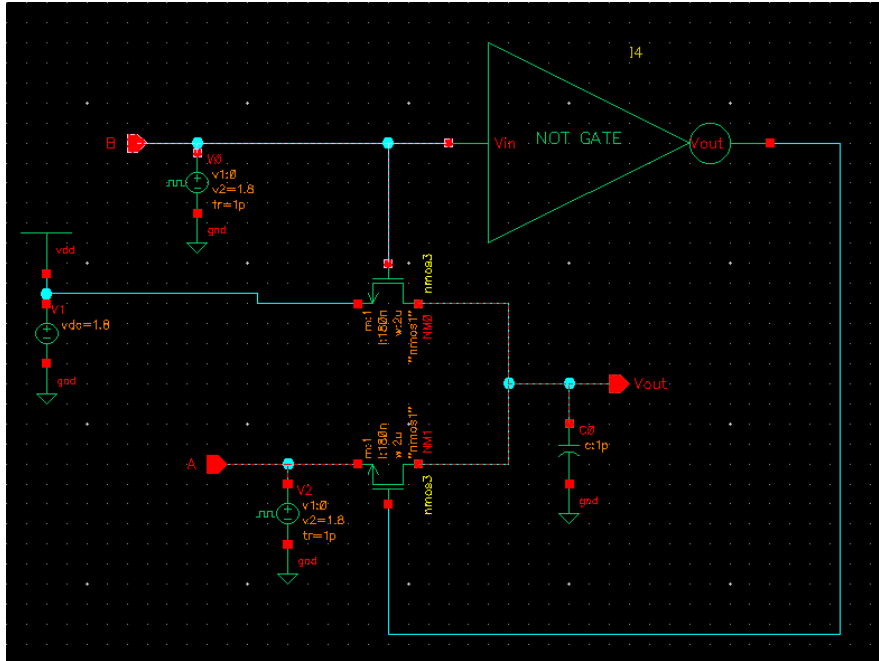
Aditya Anirudh - 2020AAPS0373H

Schematics:

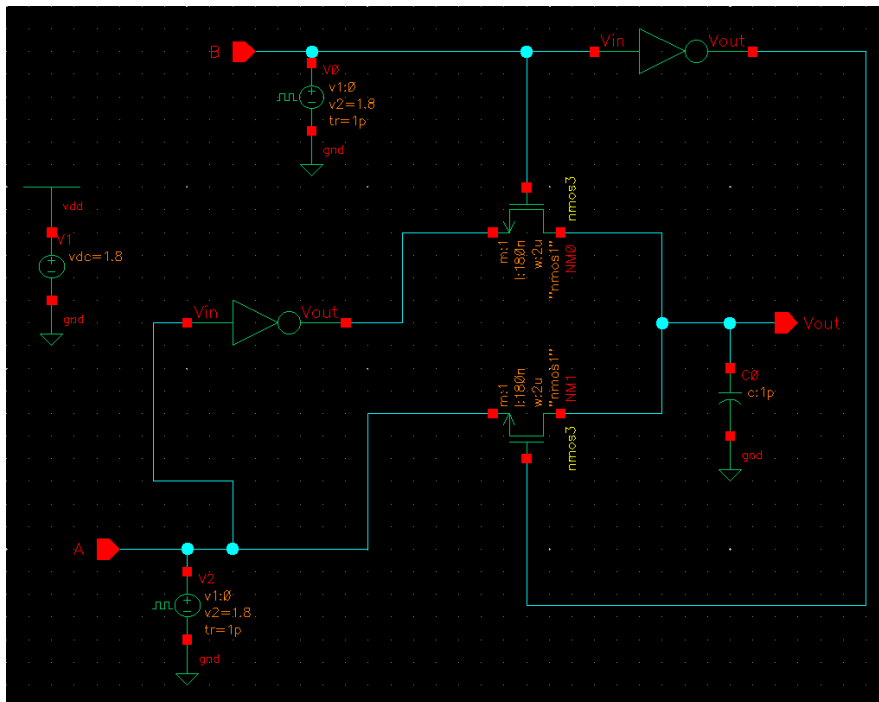
AND GATE using PTL:-



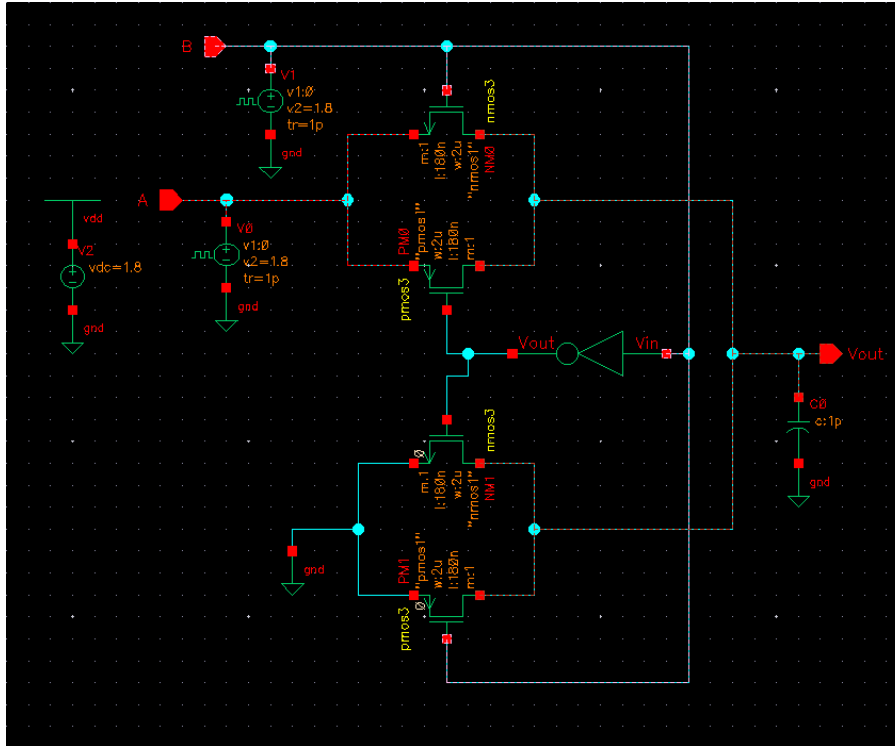
OR GATE using PTL:-



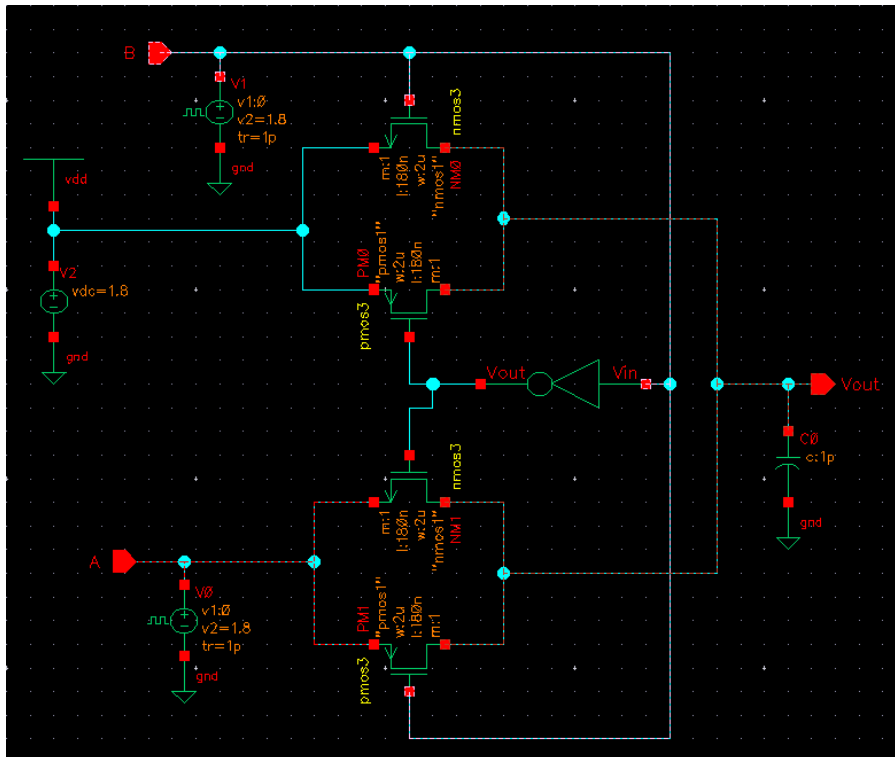
XOR GATE using PTL:-



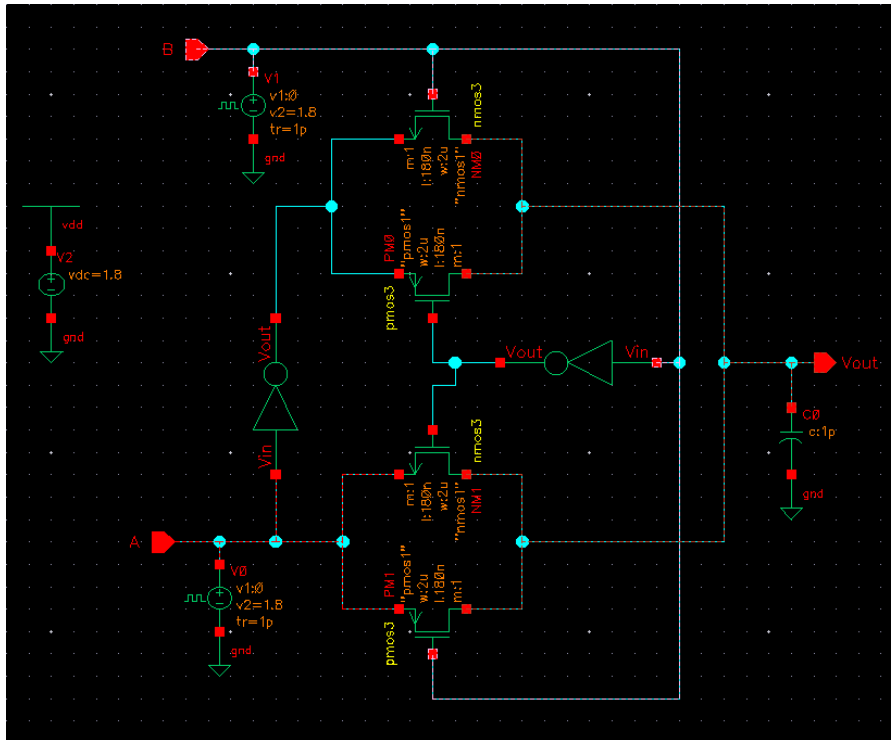
AND GATE using TGL:-



OR GATE using TGL:-

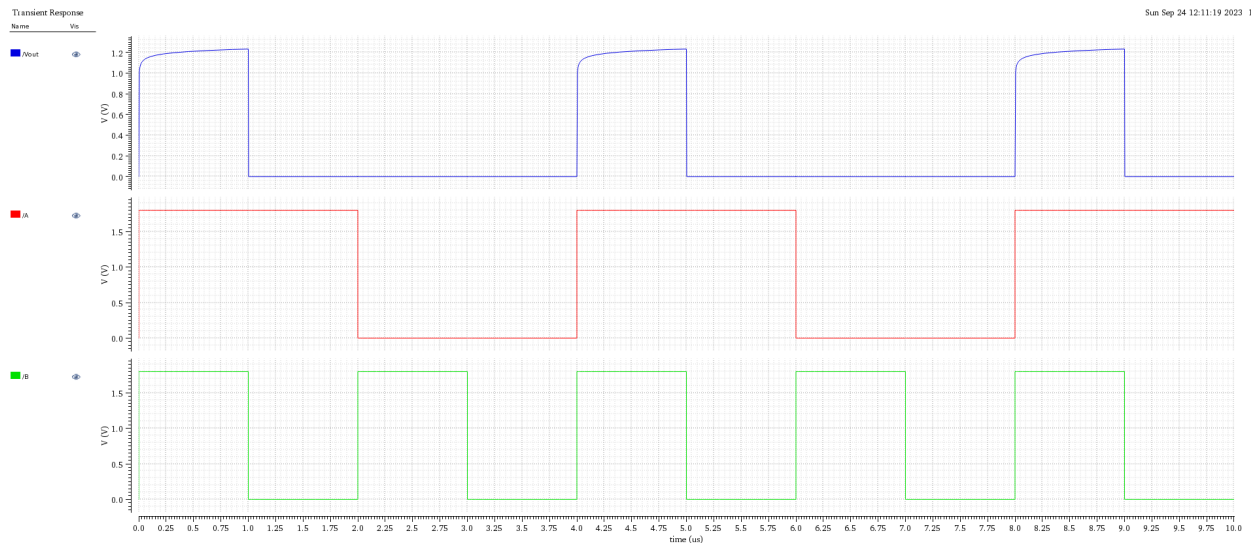


## XOR GATE using TGL:-

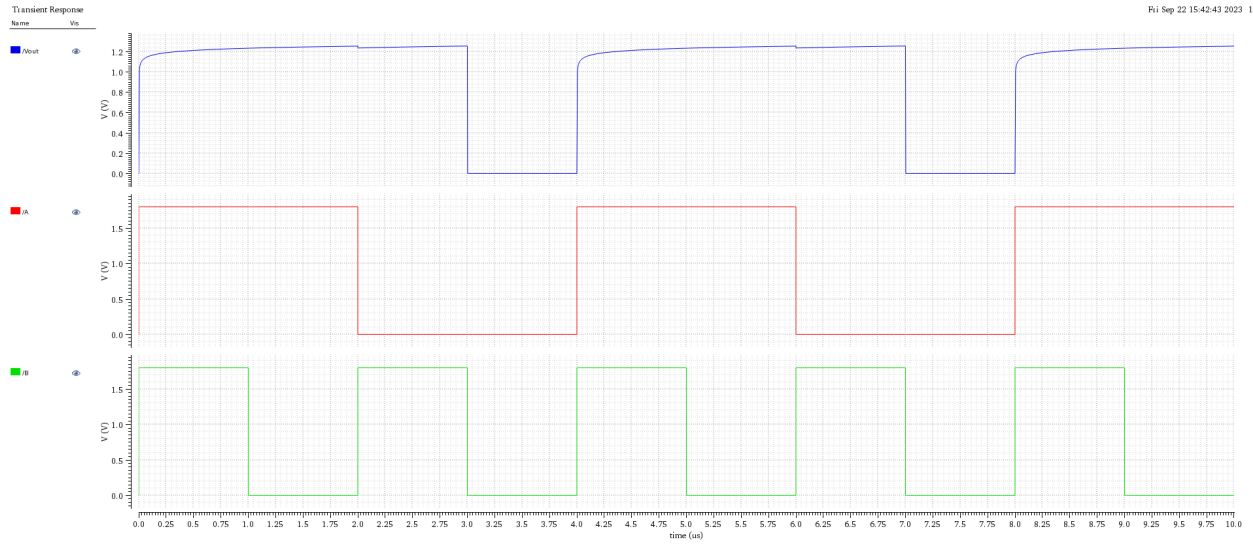


## Waveforms:

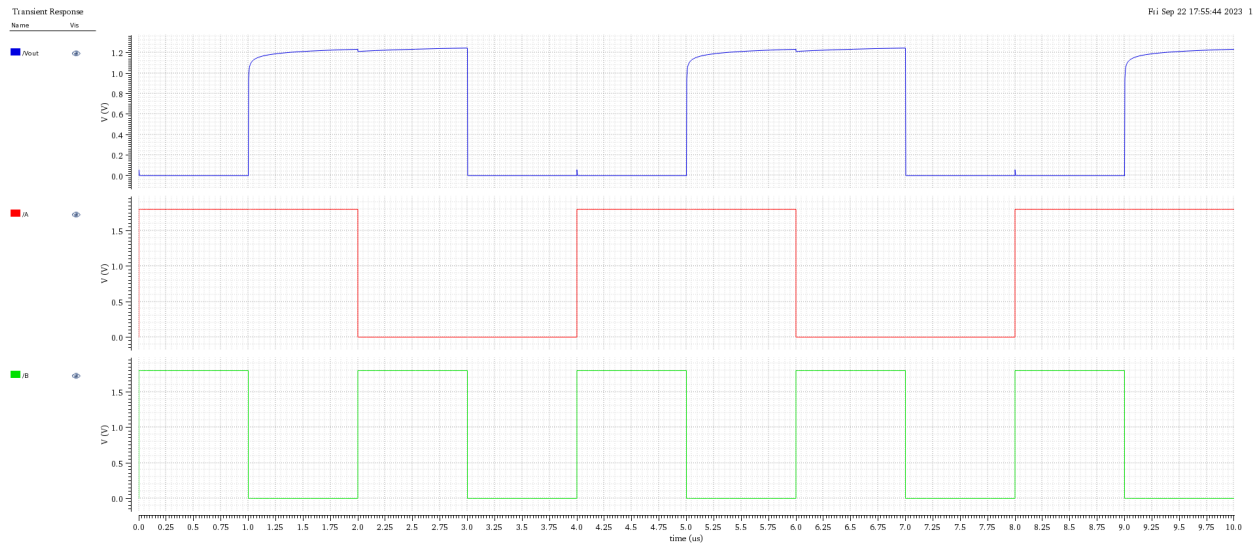
### AND GATE using PTL:-



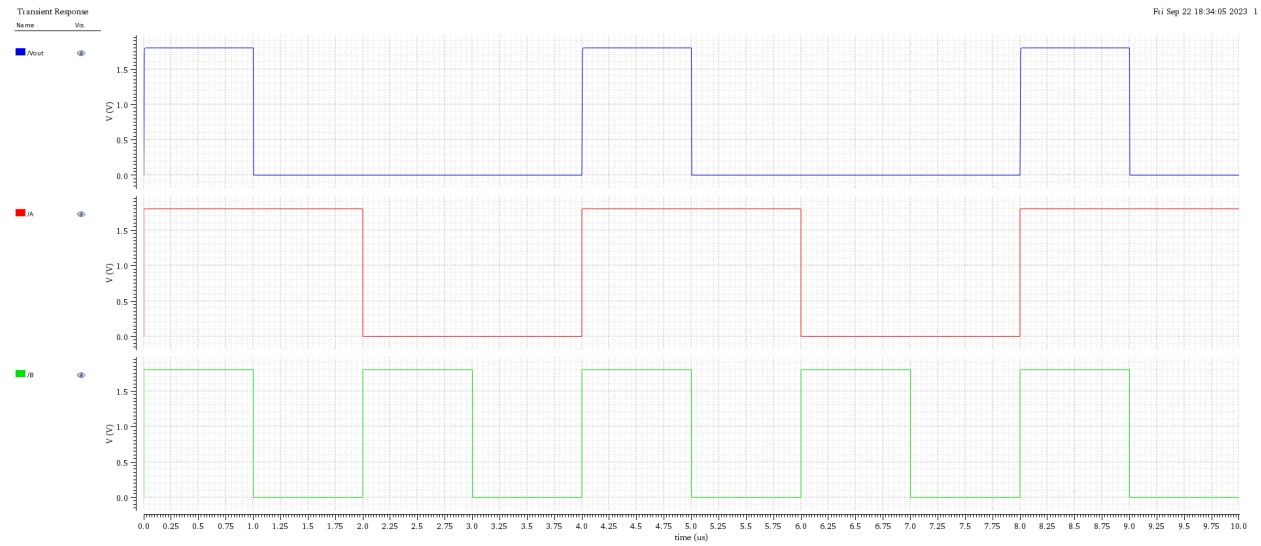
### OR GATE using PTL:-



## XOR GATE using PTL:-



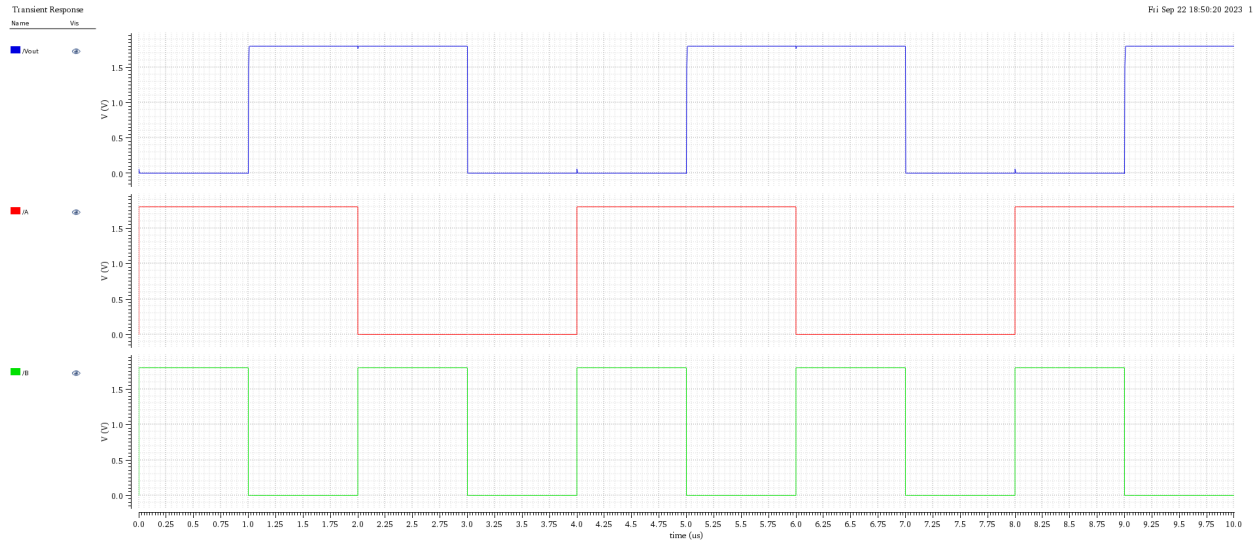
## AND GATE using TGL:-



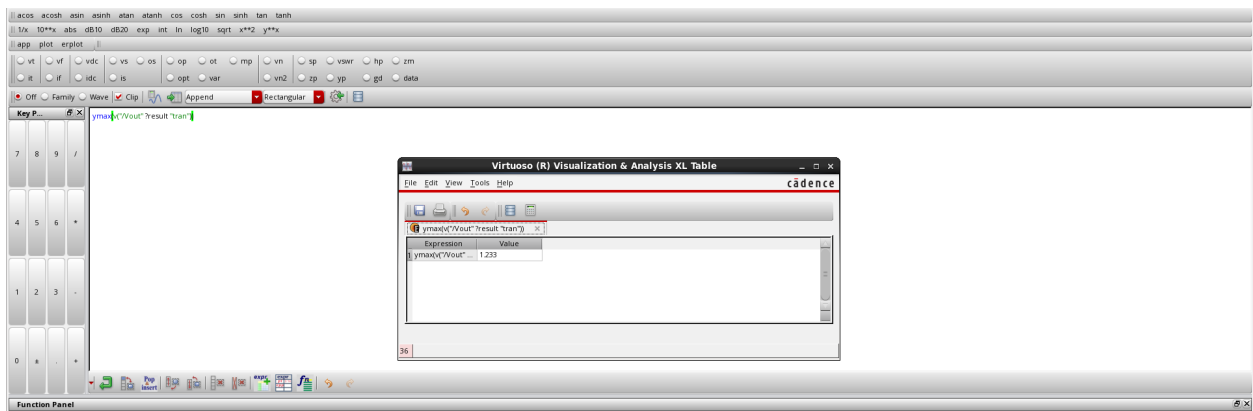
OR GATE using TGL:-



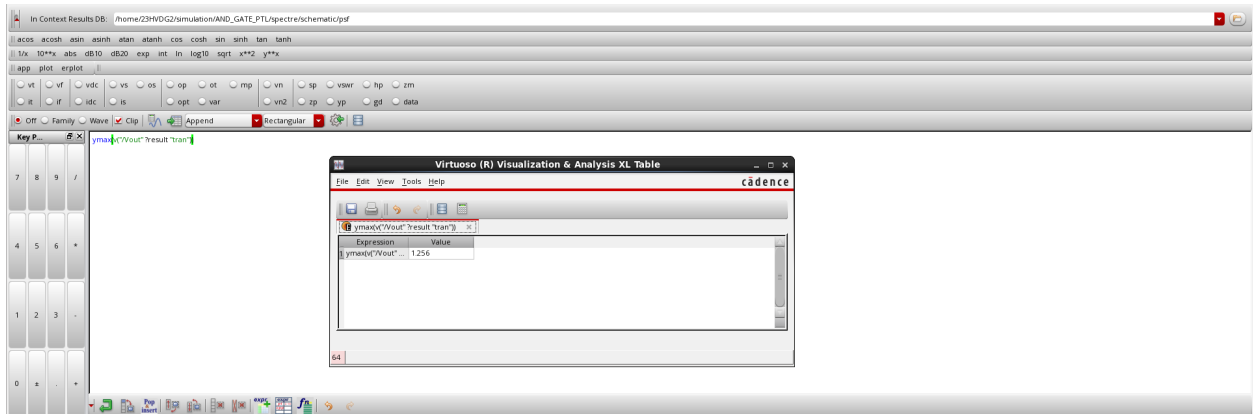
XOR GATE using TGL:-



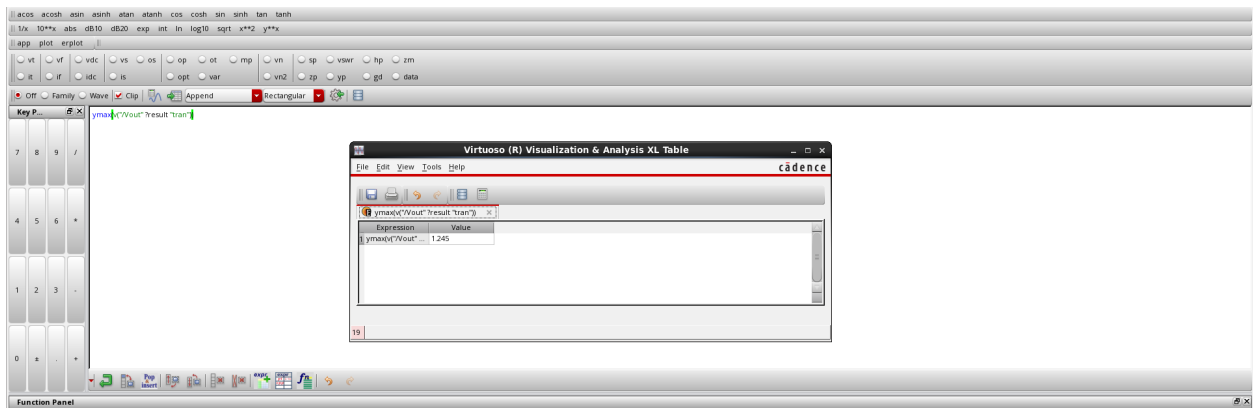
Observations:  
*Voltage Swing -*  
 AND GATE using PTL:-



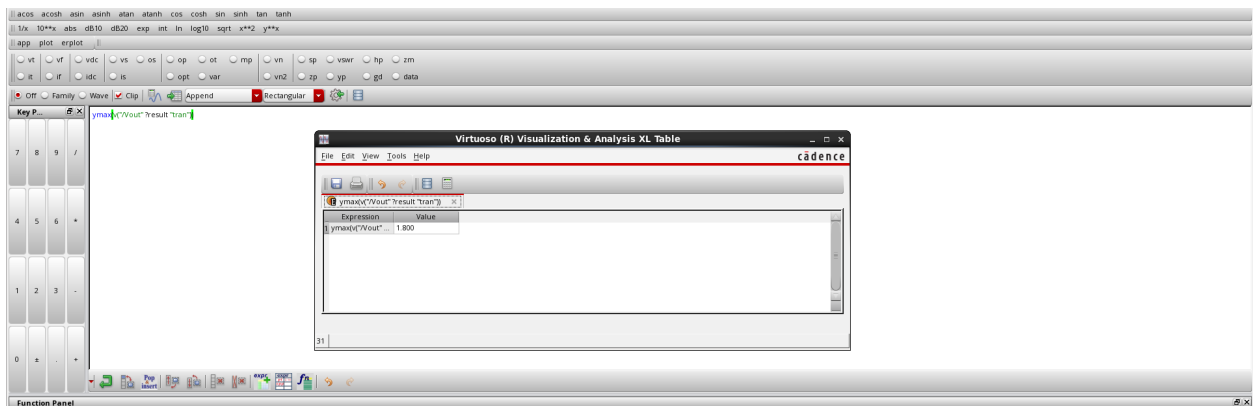
OR GATE using PTL:-



## XOR GATE using PTL:-

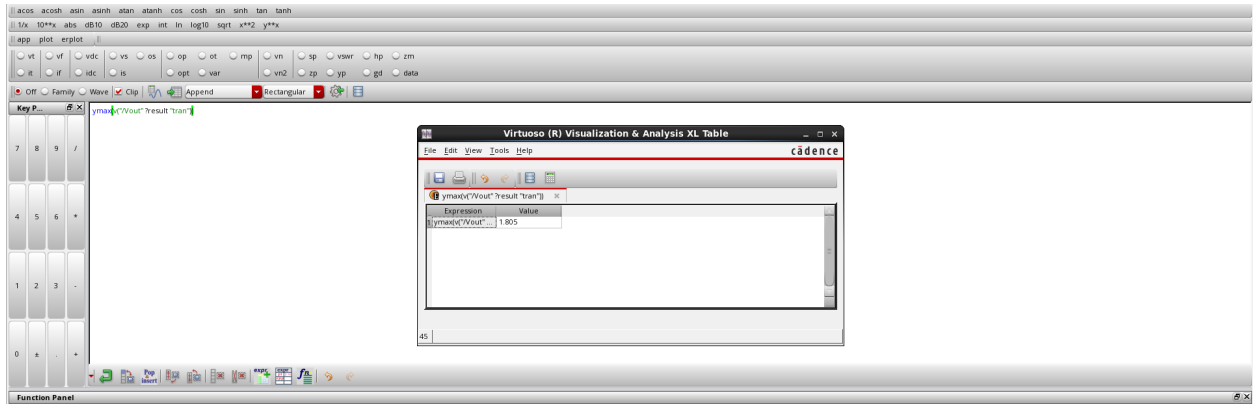


## AND GATE using TGL:-

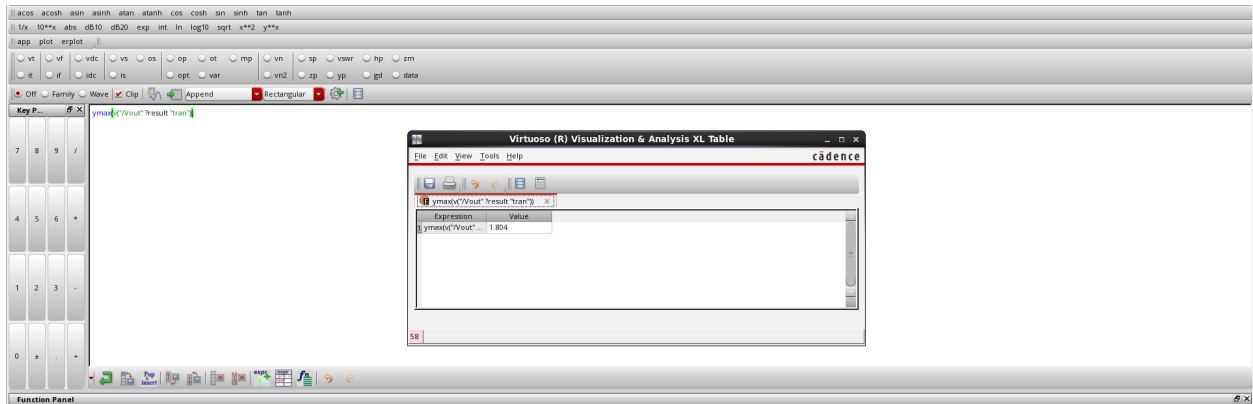


## OR GATE using TGL:-

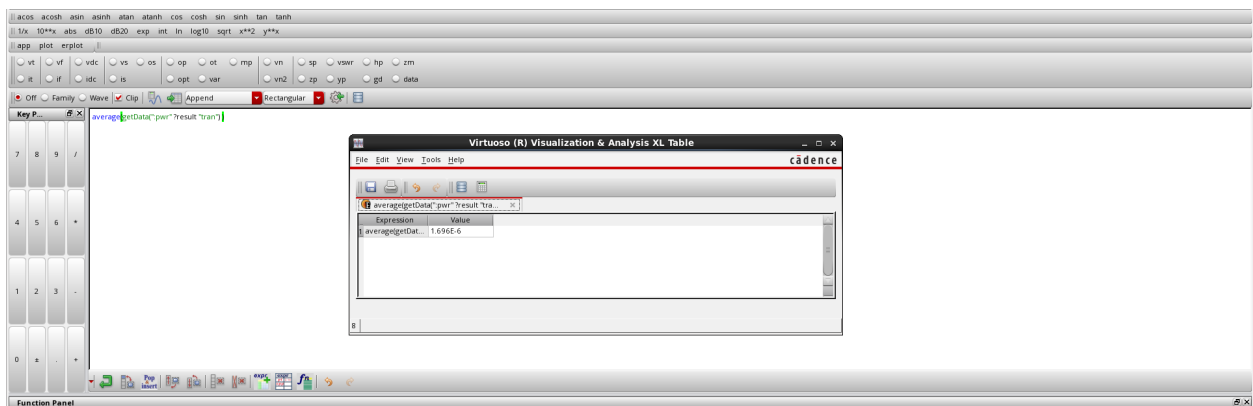




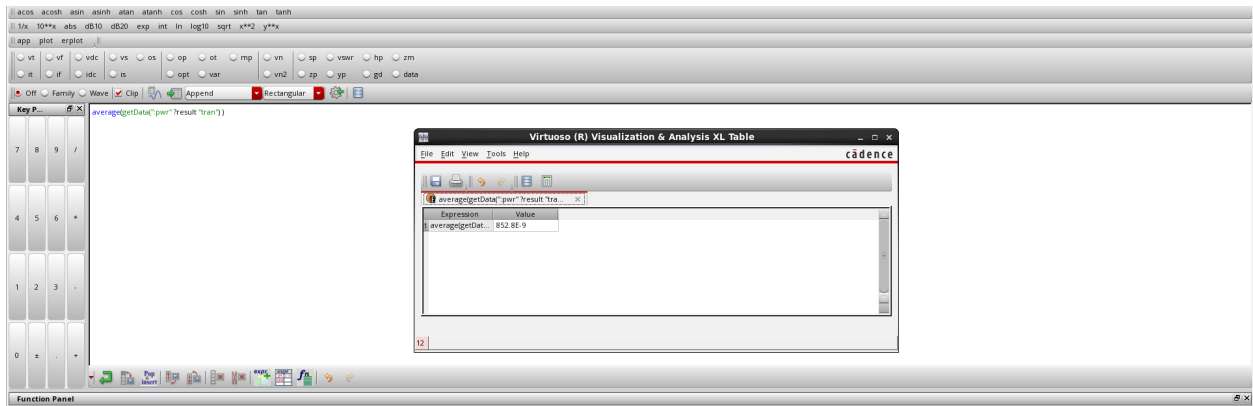
XOR GATE using TGL:-



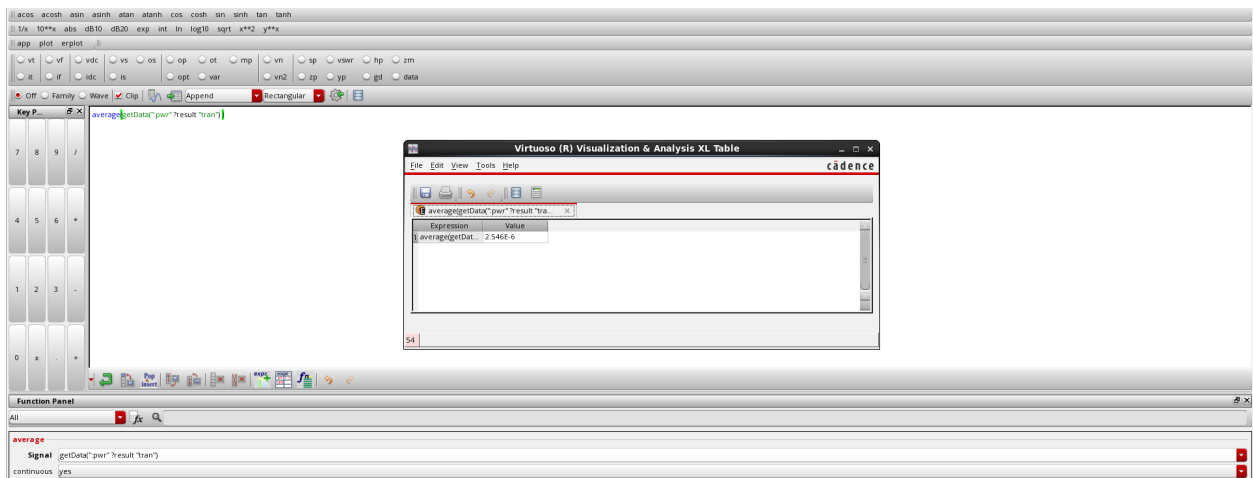
Power dissipation -  
AND GATE using CMOS:-



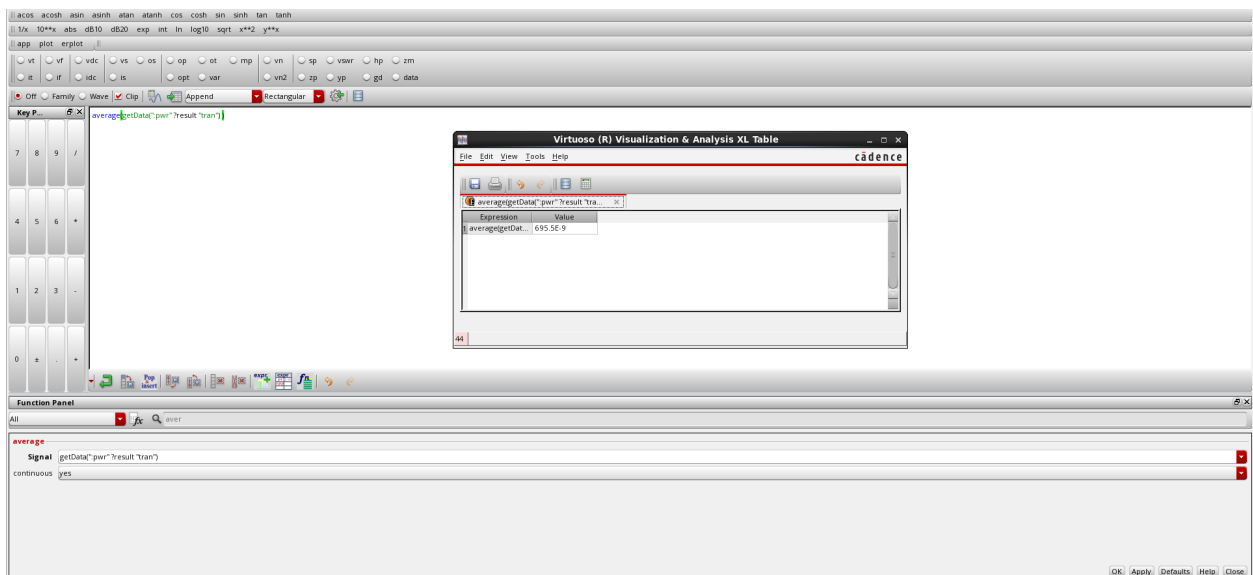
OR GATE using CMOS:-



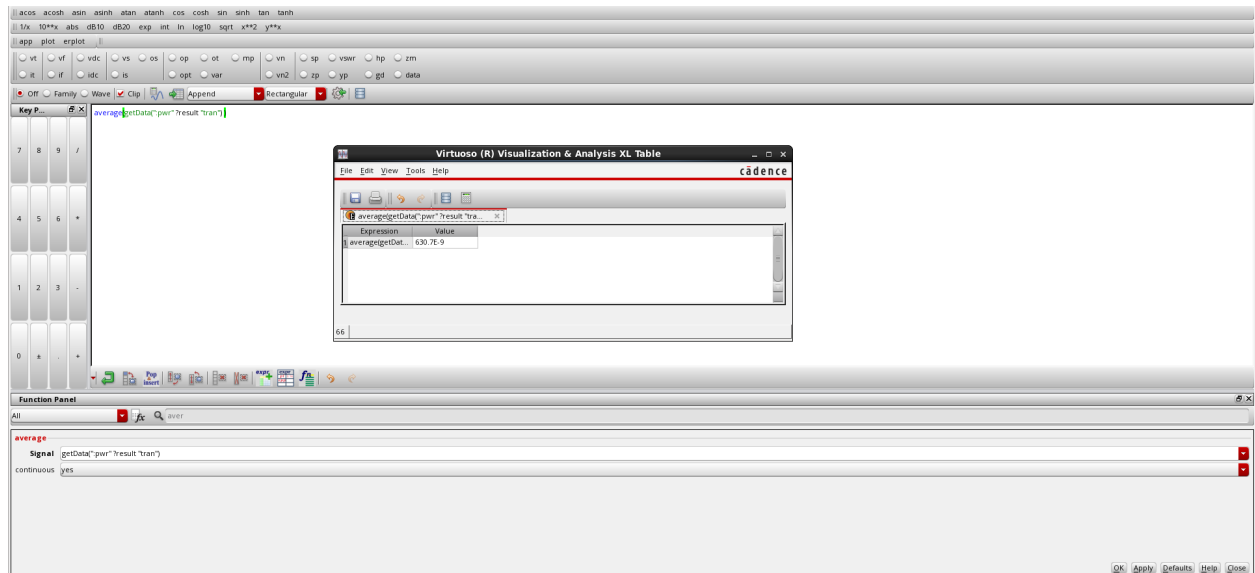
## XOR GATE using CMOS:-



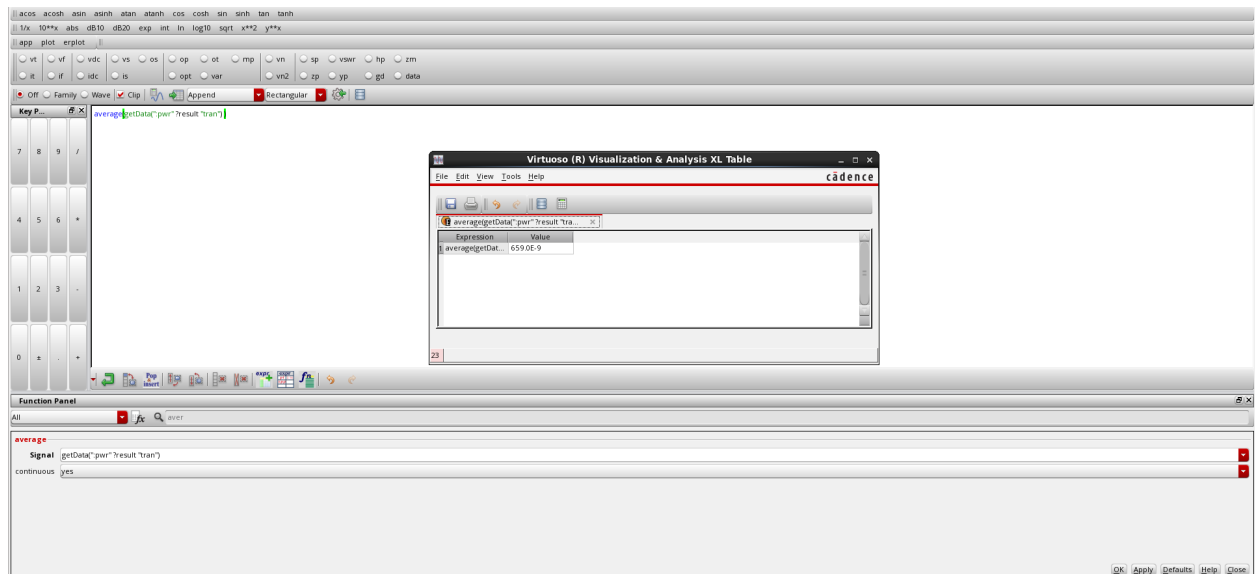
## AND GATE using PTL:-



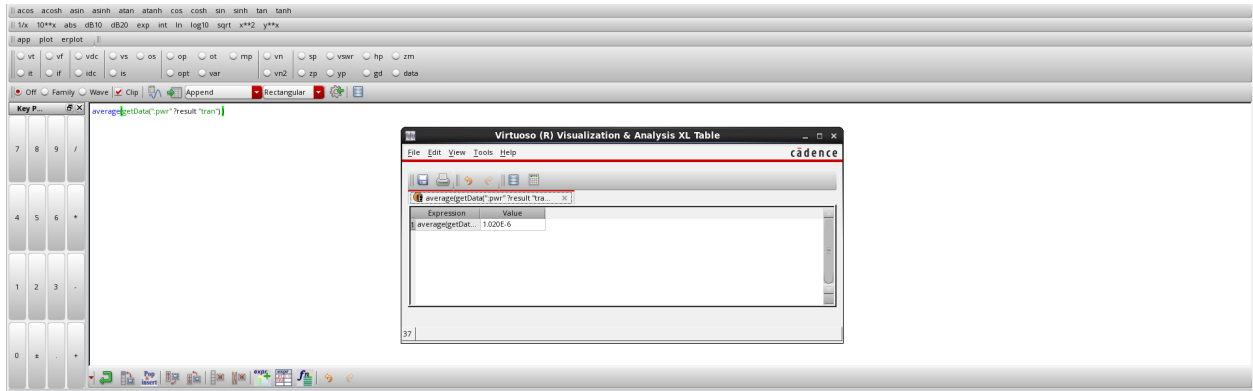
## OR GATE using PTL:-



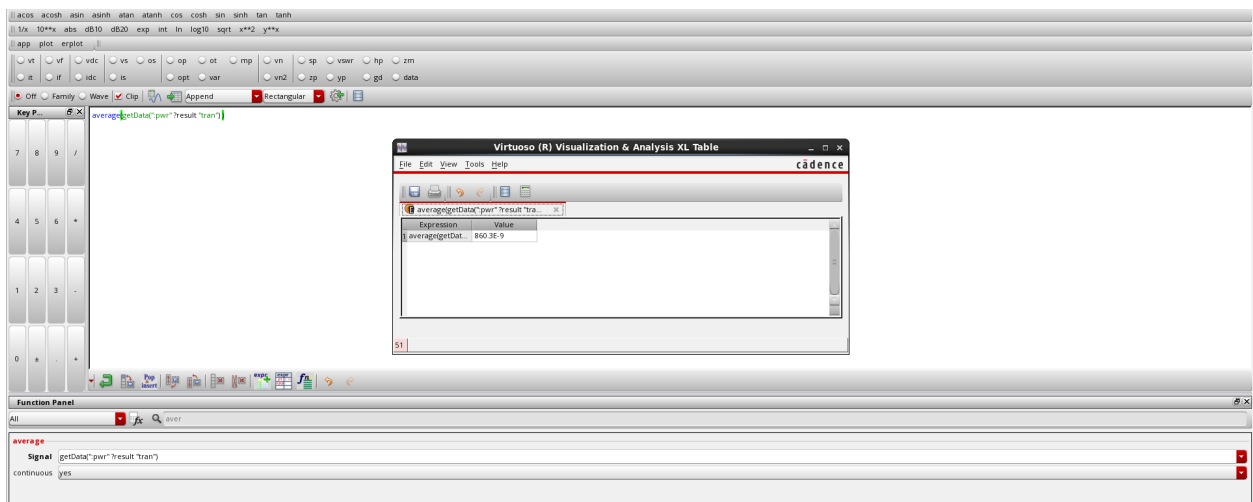
## XOR GATE using PTL:-



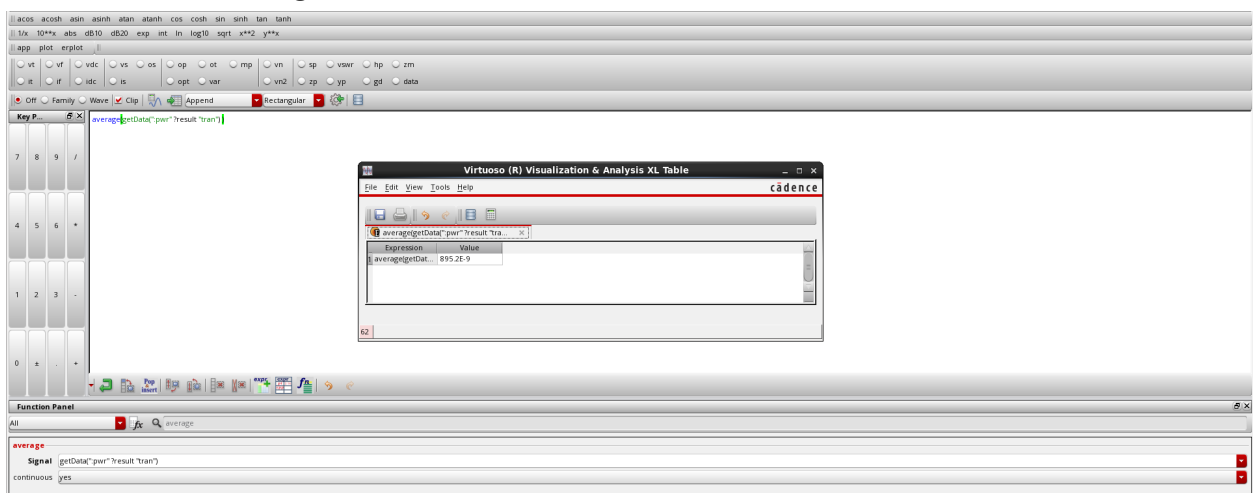
## AND GATE using TGL:-



## OR GATE using TGL:-

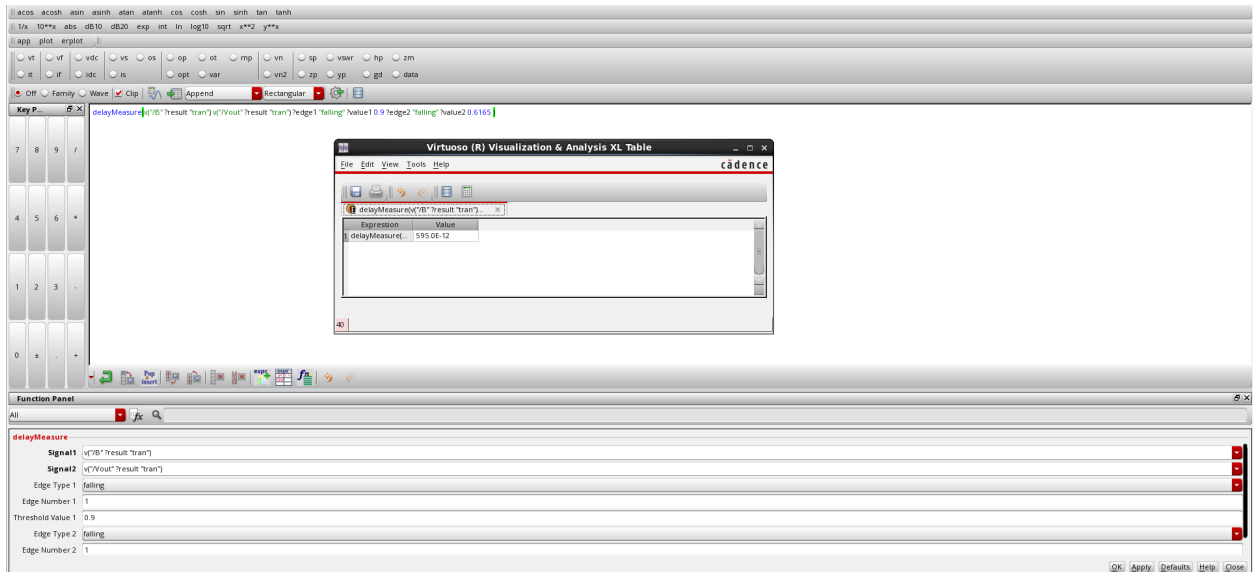


## XOR GATE using TGL:-

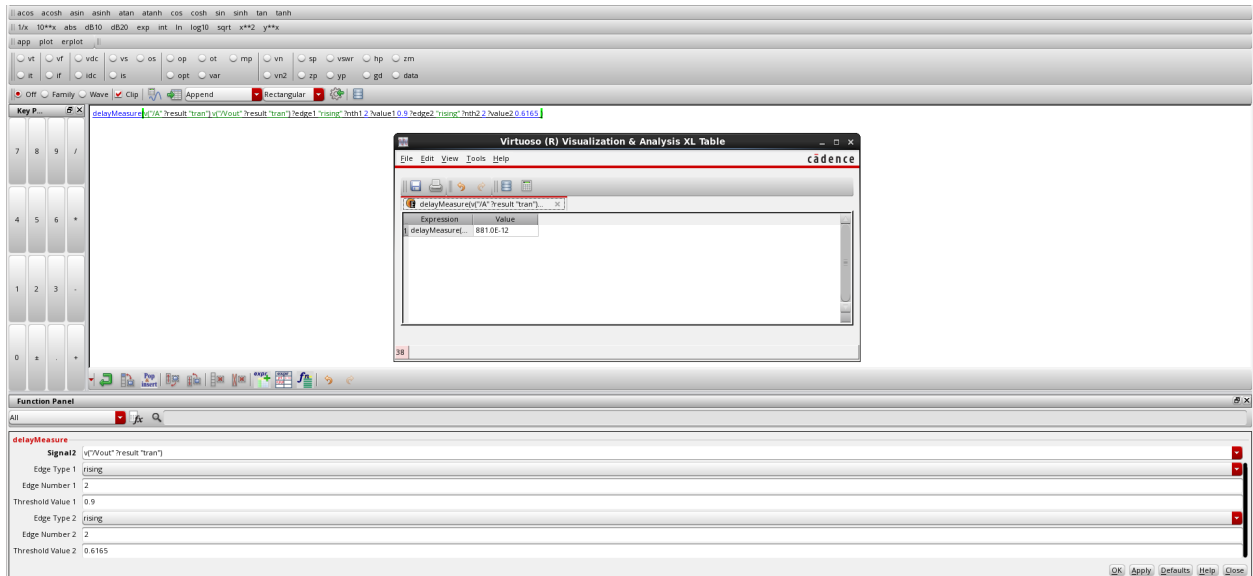


## Delay - AND GATE using PTL:-

$t_{pHL}$ :

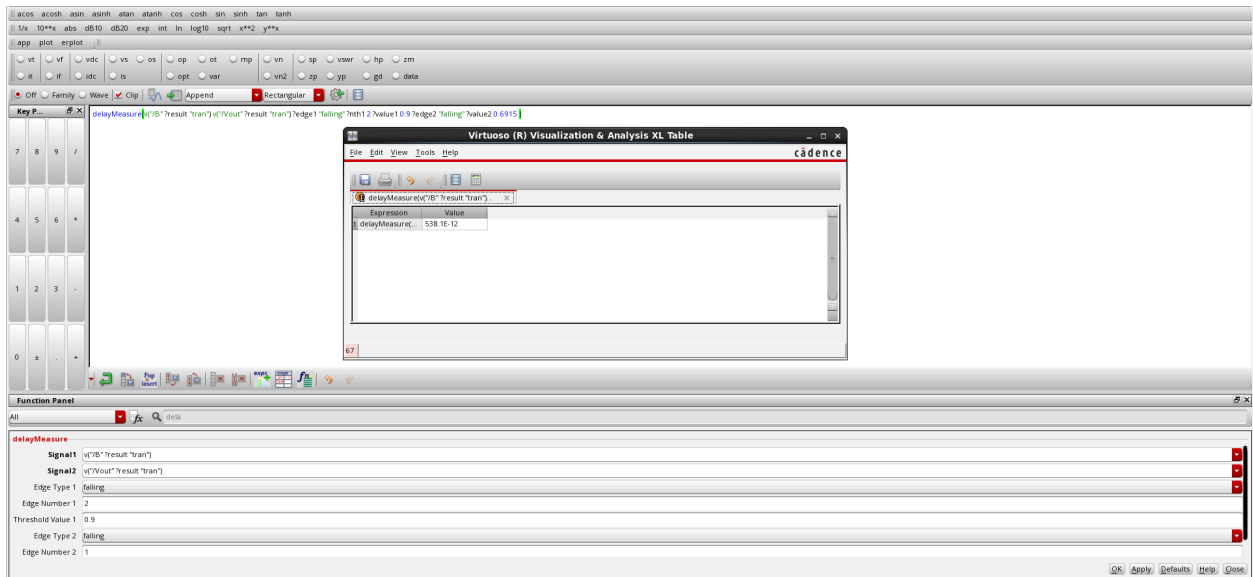


$t_{pLH}$ :

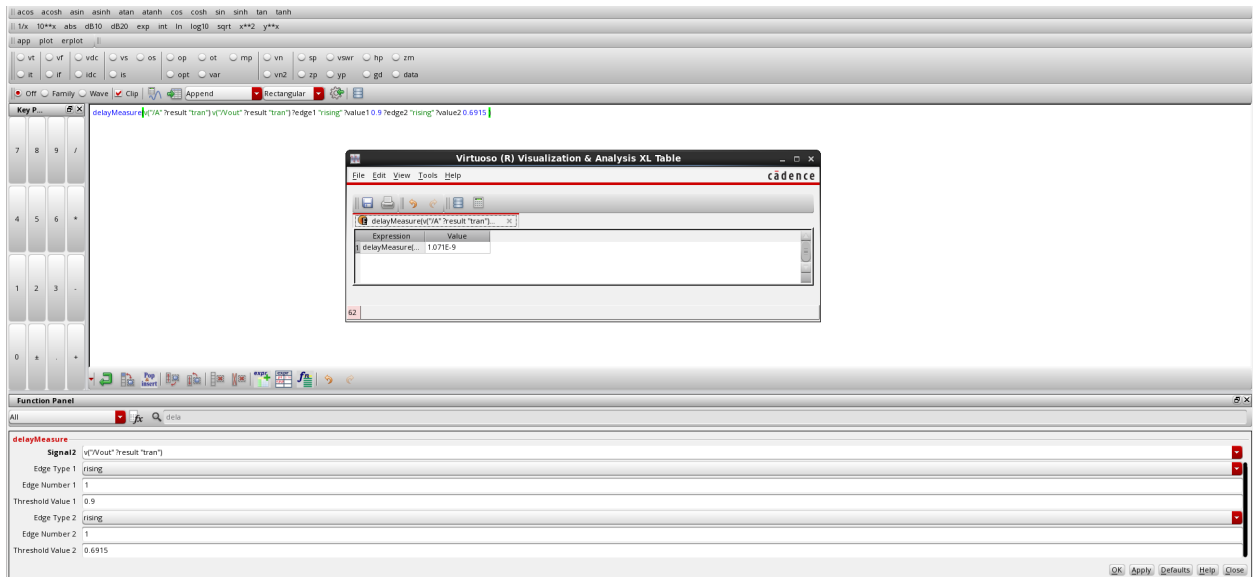


## OR GATE using PTL:-

$t_{pHL}$ :

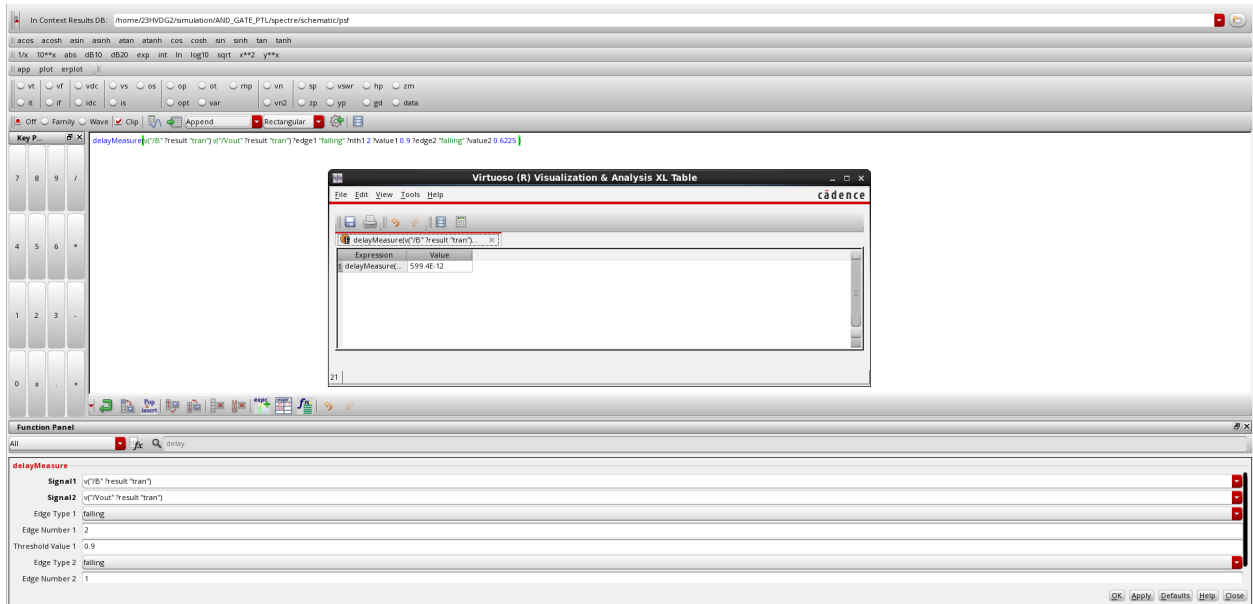


$t_{pLH}$ :

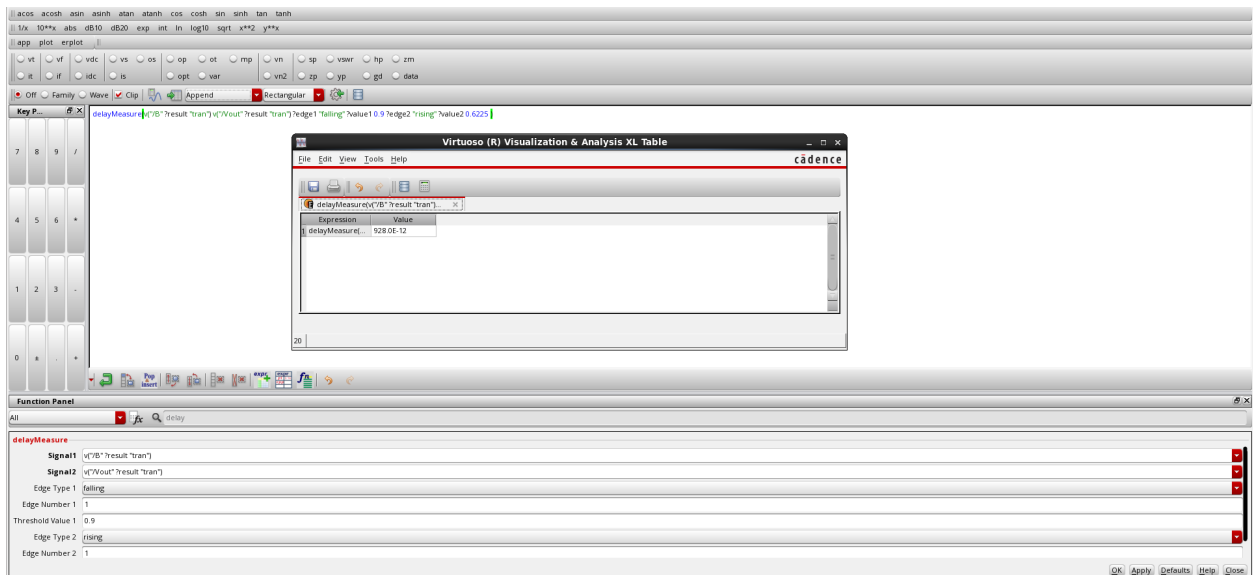


XOR GATE using PTL:-

$t_{pHL}$ :

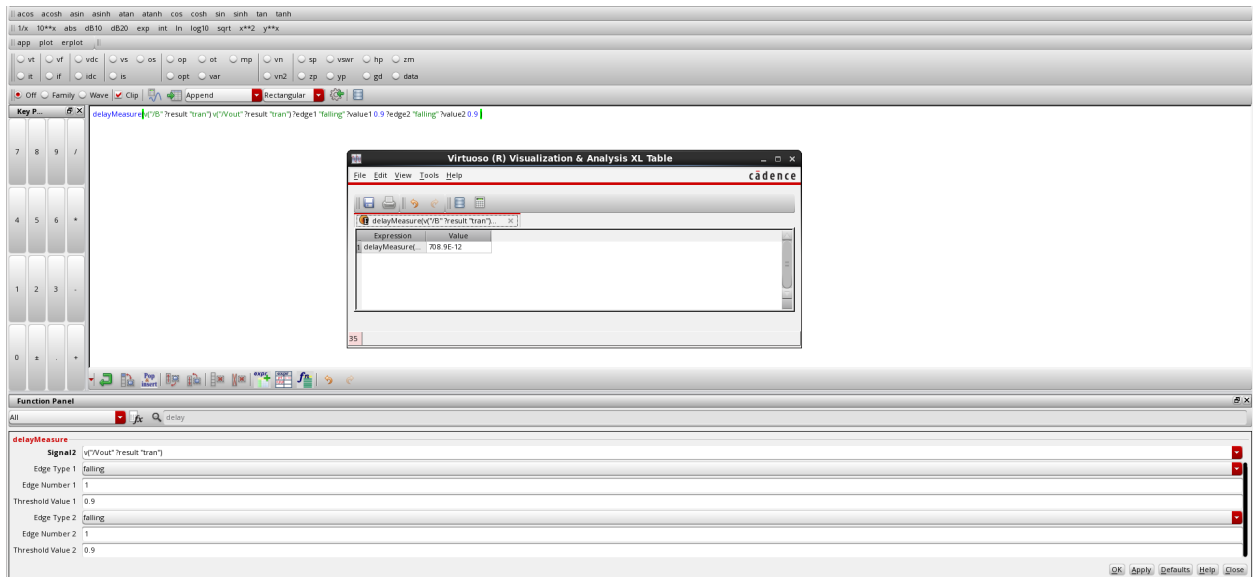


$t_{PLH}$ :

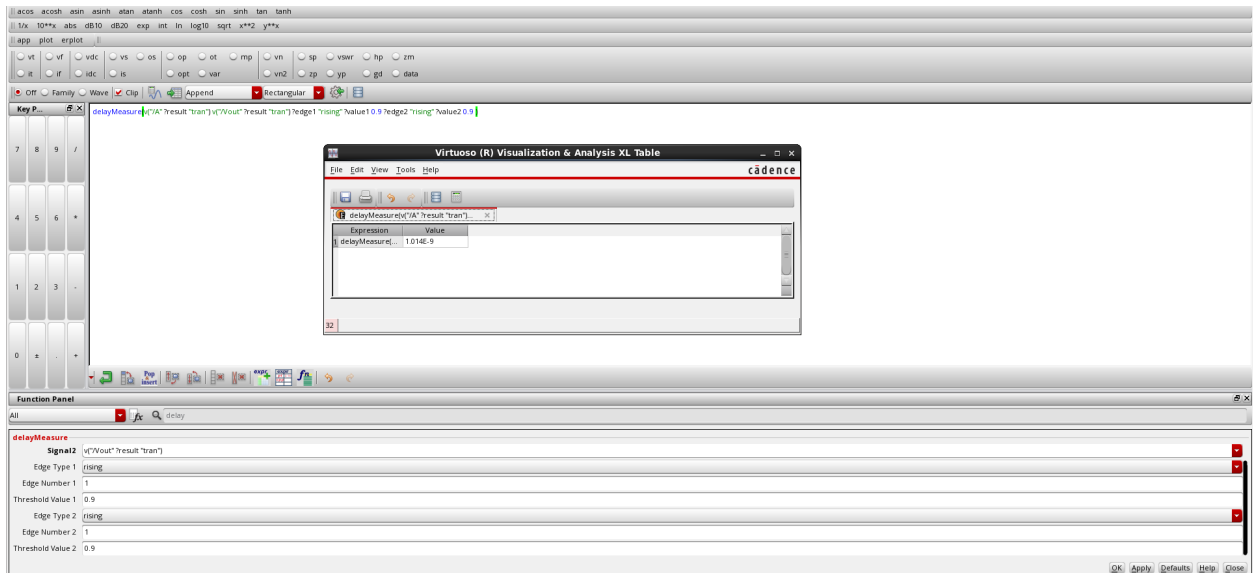


AND GATE using TGL:-

$t_{pHL}$ :



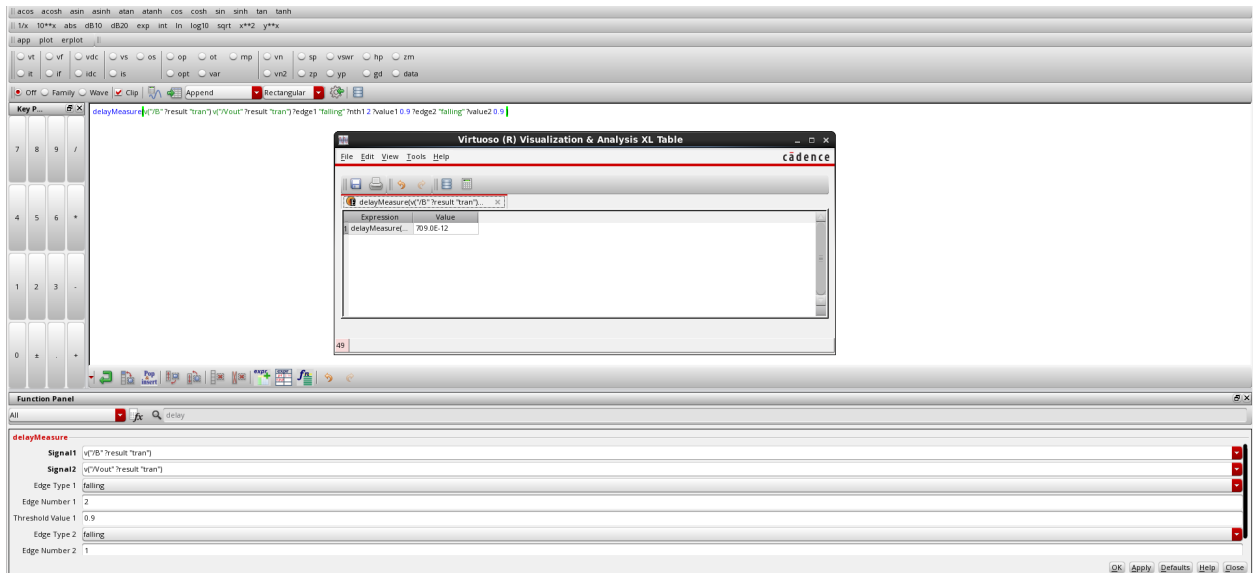
$t_{pLH}$ :



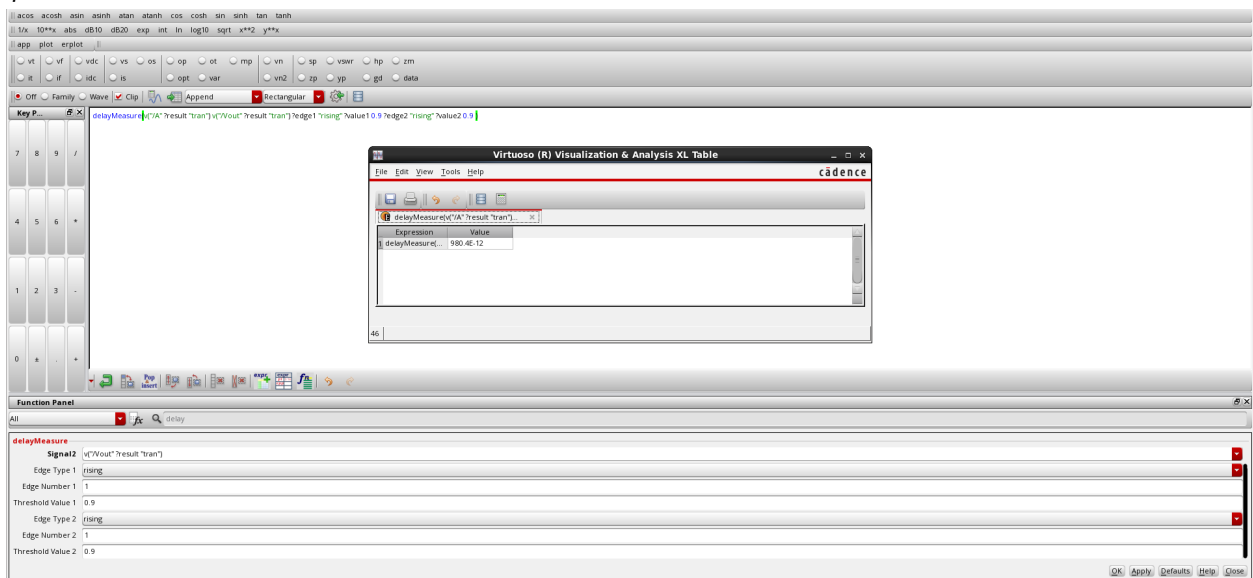
OR GATE using TGL:-

$t_{pHL}$ :





$t_{PLH}$ :



XOR GATE using TGL:-

$t_{pHL}$ :

|| acos acosh asin asinh atan atanh cos cosh sin sinh tan tanh  
|| 1/x 10\*\*x abs dB10 dB20 exp int ln log10 sqrt x\*\*2 y\*\*x  
|| app. plot. exp. plot

vt vt vdc vs os op ot mp vn sp vswr hp zm  
it if ldc ls opt var vn2 zp yp gd data

Off Family Wave Clip Append Rectangular

Key P... delayMeasure["(B"result"train")v("Vout"result"train")edge1"falling"threshold1 0.9"edge2"falling"threshold2 0.9"]

7 8 9 /  
4 5 6 \*  
1 2 3 -  
0 + +

Virtuoso (R) Visualization & Analysis XL Table  
cadence

Expression	Value
delayMeasure...	707.46-12

60

Function Panel

All delay

delayMeasure

Signal2 v("Vout"result"train")

Edge Type 1 falling

Edge Number 1 2

Threshold Value 1 0.9

Edge Type 2 falling

Edge Number 2 1

Threshold Value 2 0.9

OK Apply Defaults Help Close

$t_{PLH}$

|| acos acosh asin asinh atan atanh cos cosh sin sinh tan tanh  
|| 1/x 10\*\*x abs dB10 dB20 exp int ln log10 sqrt x\*\*2 y\*\*x  
|| app. plot. exp. plot

vt vt vdc vs os op ot mp vn sp vswr hp zm  
it if ldc ls opt var vn2 zp yp gd data

Off Family Wave Clip Append Rectangular

Key P... delayMeasure["(B"result"train")v("Vout"result"train")edge1"falling"threshold1 0.9"edge2"rising"threshold2 0.9"]

7 8 9 /  
4 5 6 \*  
1 2 3 -  
0 + +

Virtuoso (R) Visualization & Analysis XL Table  
cadence

Expression	Value
delayMeasure...	1.011E-9

59

Function Panel

All delay

delayMeasure

Signal2 v("Vout"result"train")

Edge Type 1 falling

Edge Number 1 1

Threshold Value 1 0.9

Edge Type 2 rising

Edge Number 2 1

Threshold Value 2 0.9

OK Apply Defaults Help Close

### Metrics Measured:

All these metrics are measured for a load capacitance = 1 pF.

<b>GATE</b>	<b>Voltage Swing</b>	<b>Power Dissipated</b>	<b>t<sub>worst</sub></b>
AND (CMOS)	1.8 V	1.696 $\mu$ W	2.146 ns
AND (PTL)	1.233 V	695.5 nW	881 ps
AND (TGL)	1.8 V	1.020 $\mu$ W	1.014 ns
OR (CMOS)	1.8 V	852.8 nW	2.099 ns
OR (PTL)	1.256 V	630.7 nW	1.071 ns
OR (TGL)	1.805 V	860.3 nW	980.4 ps
XOR (CMOS)	1.8 V	2.546 $\mu$ W	4.105 ns
XOR (PTL)	1.245 V	659 nW	928 ps
XOR (TGL)	1.804 V	895.2 nW	1.011 ns

### Inferences:

1. When the same gate is constructed once using pass transistors and then using transmission gates, the delay involved in transmission gate logic is larger because more transistors are present (as compared to PTL) leading to larger resistance in the RC network. Also, the power dissipation is larger for transmission gate logic style because of similar reasons.
2. Voltage swing in Pass Transistor logic is reduced while in transmission gate style, we still obtain a rail-to-rail swing. This is because in pass transistors we use only NMOS transistors which are weak at passing a 1-logic level. That is, they can pass a

maximum voltage of ' $V_{DD} - V_{T,n}$ '. While by connecting NMOS (strong passer of '0') and PMOS (strong passer of '1'), we can get a rail-to-rail swing in transmission gates.

3. The power dissipation and the delay is the largest in CMOS circuits because of the large number of PMOS and NMOS transistors involved in building the logic network.

### Conclusion:

In this experiment, we learnt how to design AND, OR, and XOR Gates using Pass Transistor and Transmission GATE Logic Styles. We also learnt how to measure the power dissipation in a circuit using transient analyses in Cadence. Finally, we drew some observations regarding the different design metrics such as power dissipation, delay, voltage swing, etc., in these different logic styles.